



BT136S-600D

4Q Triac

Rev. 04 — 31 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

1.3 Applications

- General purpose motor control
- General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	-	25	A
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 107\text{ °C}$; see Figure 1 ; see Figure 3 ; see Figure 2	-	-	4	A

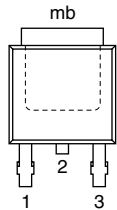
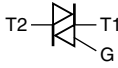


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; see Figure 7	-	2	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; see Figure 7	-	2.5	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; see Figure 7	-	2.5	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; see Figure 7	-	5	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; see Figure 9	-	1.2	10	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2 [1]		
3	G	gate		
mb	T2	mounting base; connected to main terminal 2		

SOT428 (DPAK)

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BT136S-600D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 107\text{ }^{\circ}\text{C}$; see Figure 1 ; see Figure 3 ; see Figure 2	-	4	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	25	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$; see Figure 4 ; see Figure 5	-	27	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse	-	3.1	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G+	-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G-	-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$; T2- G-	-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$; T2- G+	-	10	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature		-	125	$^{\circ}\text{C}$

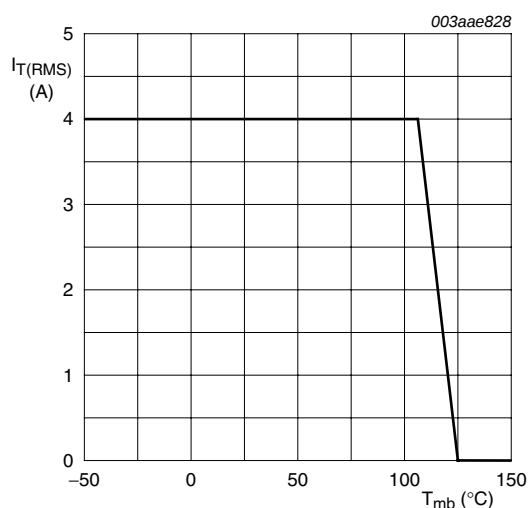


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

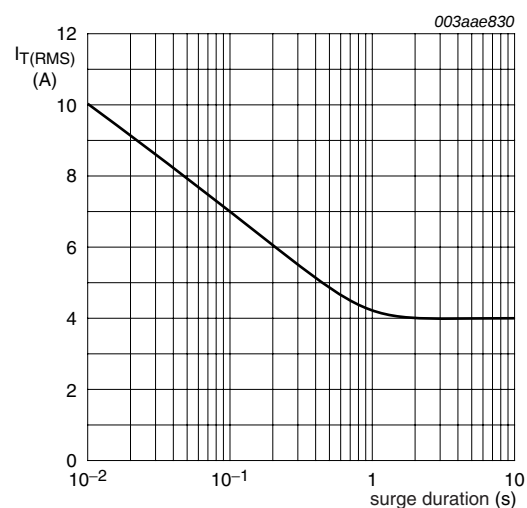
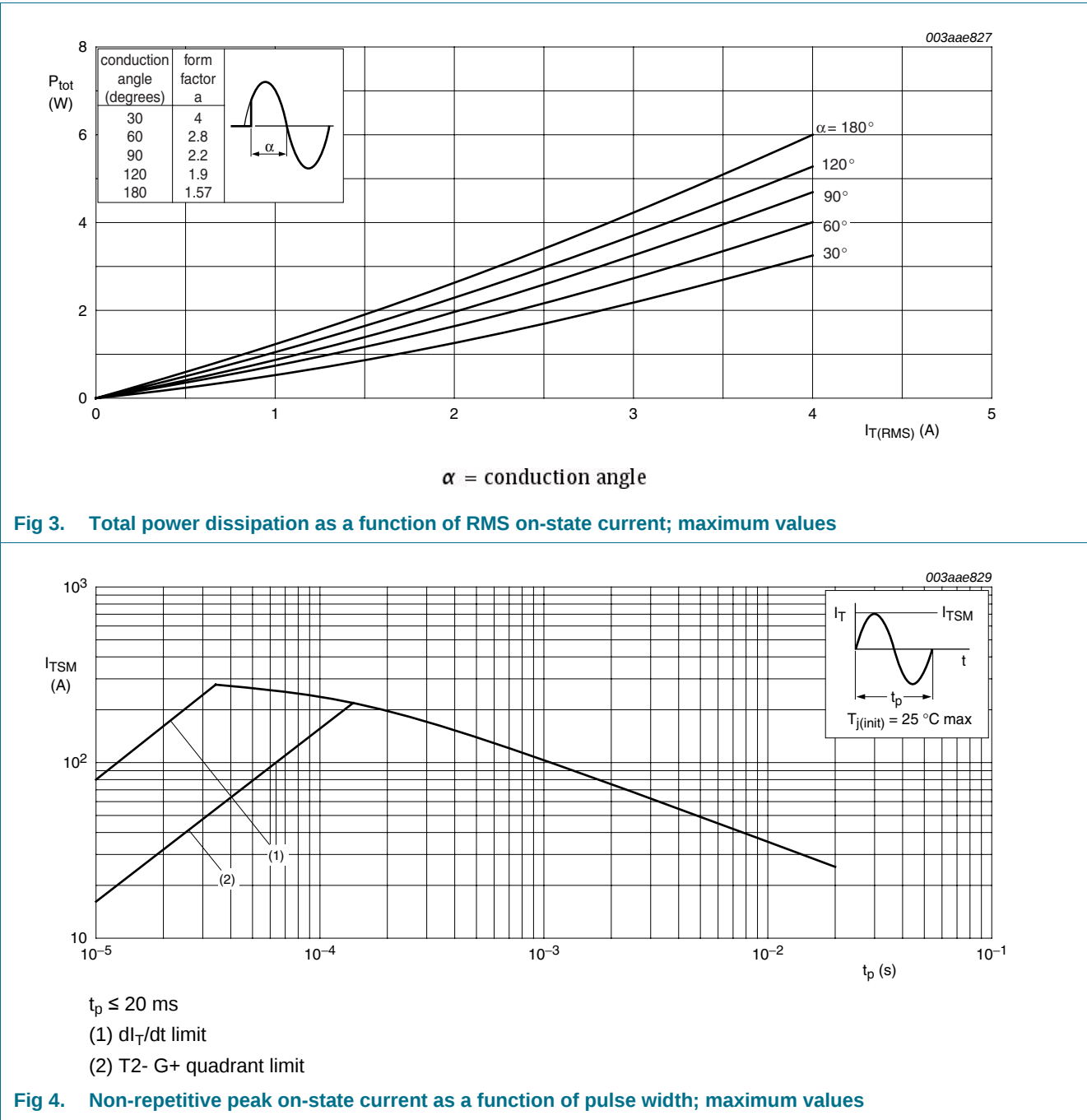


Fig 2. RMS on-state current as a function of surge duration; maximum values



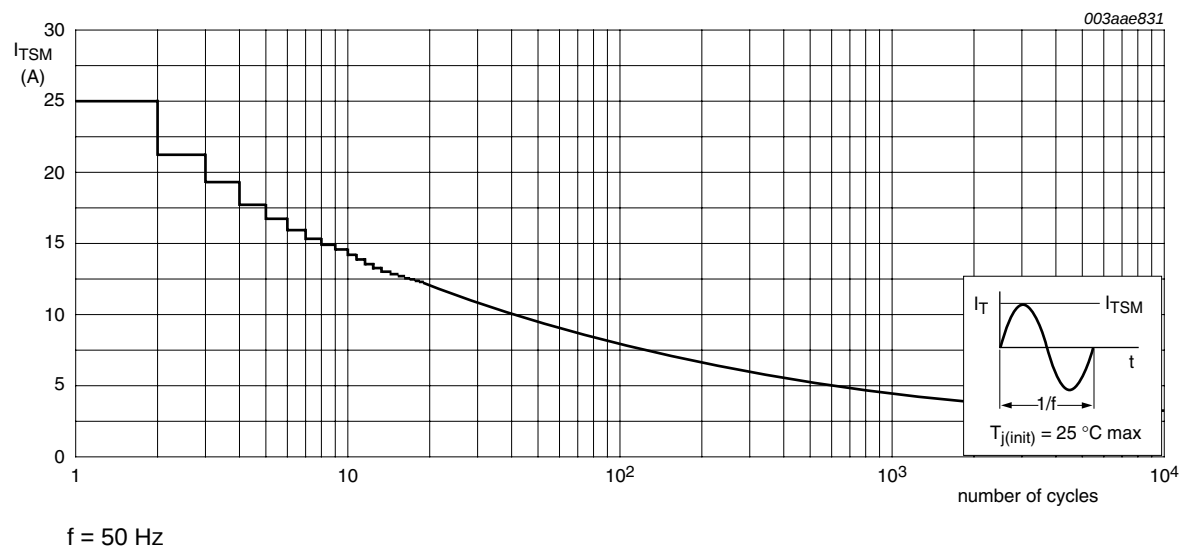


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	3	K/W
		half cycle; see Figure 6	-	-	3.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	75	-	K/W

[1] printed circuit board (FR4) mounted; standard footprint, single-sided copper, tin-plated

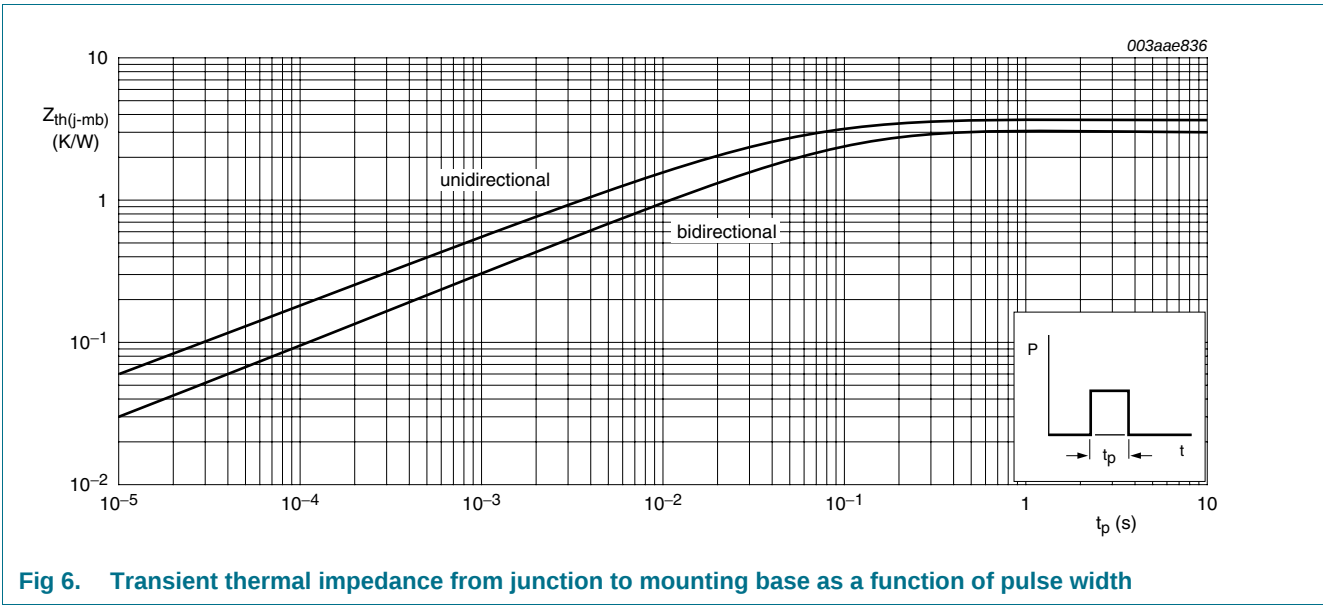


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	-	2	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	-	2.5	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	-	2.5	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 7	-	5	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	1.6	10	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	4.5	15	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	1.2	10	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; see Figure 8	-	2.2	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 9	-	1.2	10	mA
V_T	on-state voltage	$I_T = 5\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 10	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 11	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; see Figure 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	-	5	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 6\text{ A}$; $V_D = 600\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

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T_j (°C)	$\frac{I_L}{I_{L(25^\circ\text{C})}}$
-40	1.7
-20	1.5
0	1.2
25	1.0
50	0.85
75	0.75
100	0.65
125	0.6

003aae837

T_j (°C)	$\frac{I_H}{I_H(25^\circ\text{C})}$
-60	1.85
-40	1.65
-20	1.45
0	1.25
20	1.05
40	0.90
60	0.78
80	0.68
100	0.60
120	0.52
140	0.45

(3) $T_i = 25^\circ\text{C}$; maximum values

Fig 10. On-state current as a function of on-state voltage

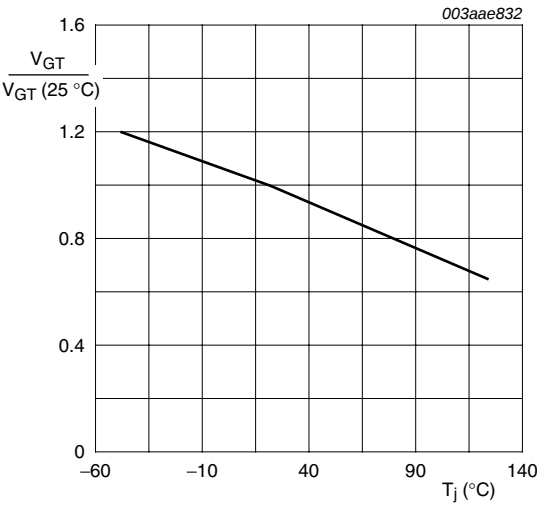


Fig 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

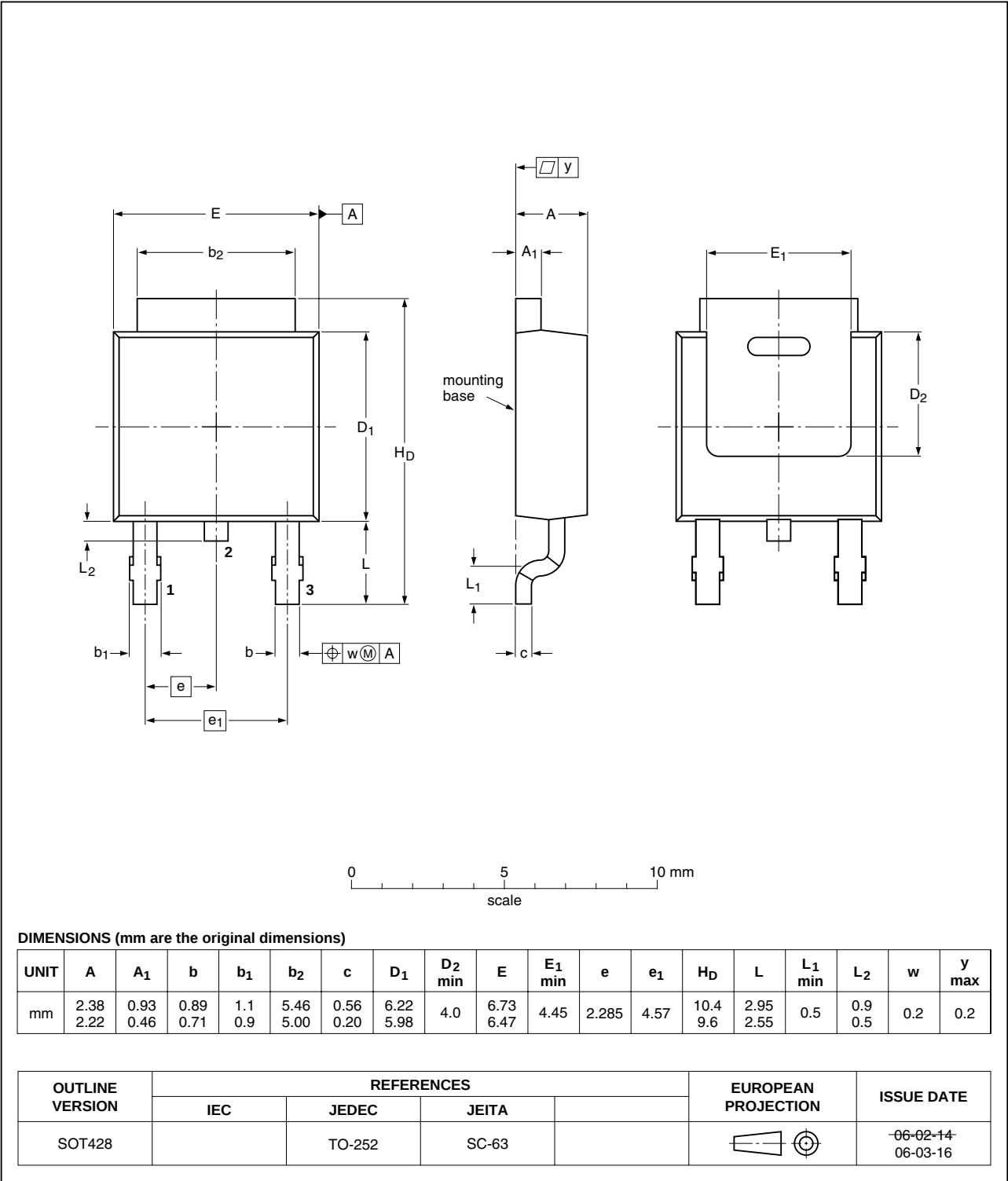


Fig 12. Package outline SOT428 (DPAK)

8. Soldering

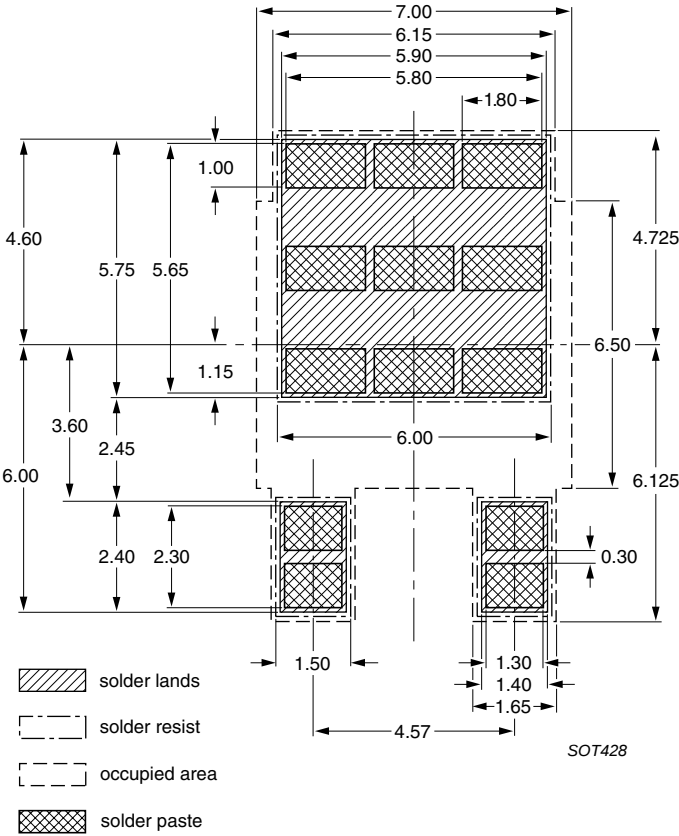


Fig 13. Reflow soldering footprint for SOT428 (DPAK)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT136S-600D v.4	20110331	Product data sheet	-	BT136S-600D v.3
Modifications:	• Various changes to content.			
BT136S-600D v.3	20101021	Product data sheet	-	BT136S_SERIES_D v.2

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Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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